MC74LCX138

Low-Voltage CMOS 3-to-8 Decoder/Demultiplexer

With 5 V−Tolerant Inputs

The MC74LCX138 is a high performance, 3−to−8 decoder/demultiplexer operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5 V allows MC74LCX138 inputs to be safely driven from 5 V devices. The MC74LCX138 is suitable for memory address decoding and other TTL level bus−oriented applications.

The MC74LCX138 high−speed 3−to−8 decoder/demultiplexer accepts three binary weighted inputs (A0, A1, A2) and, when enabled, provides eight mutually exclusive active−LOW outputs ($\overline{O0}$–$\overline{O7}$). The LCX138 features three Enable inputs, two active−LOW ($\overline{E1}$, $\overline{E2}$) and one active−HIGH (E3). All outputs will be HIGH unless $\overline{E1}$ and $\overline{E2}$ are LOW, and E3 is HIGH. This multiple enabled function allows easy parallel expansion of the device to a 1−of−32 (5 lines to 32 lines) decoder with just four LCX138 devices and one inverter (see Figure 1). The LCX138 can be used as an 8−output demultiplexer by using one of the active−LOW Enable inputs as the data input and the other Enable inputs as strobes. The Enable inputs which are not used must be permanently tied to their appropriate active−HIGH or active−LOW state.

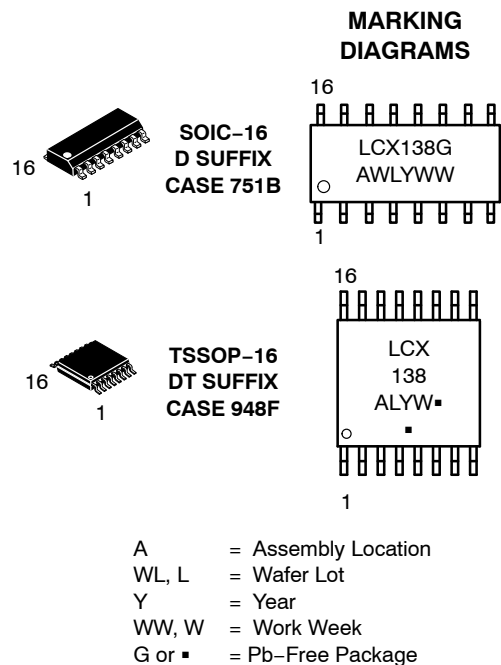Current drive capability is 24 mA at the outputs.

Features

- Designed for 2.3 V to 3.6 V V_{CC} Operation
- 5 V Tolerant Inputs − Interface Capability With 5 V TTL Logic
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current (10 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V
  Machine Model >200 V
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

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MARKING DIAGRAMS

SOIC−16
D SUFFIX
CASE 751B

LCX138G
AWLYWW

TSSOP−16
DT SUFFIX
CASE 948F

LCX
138
ALYW■

A	= Assembly Location
WL, L	= Wafer Lot
Y	= Year
WW, W	= Work Week
G or ■	= Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.
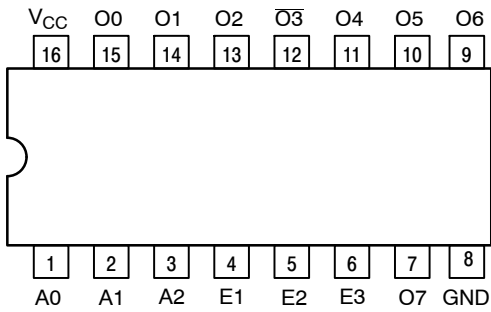
MC74LCX138
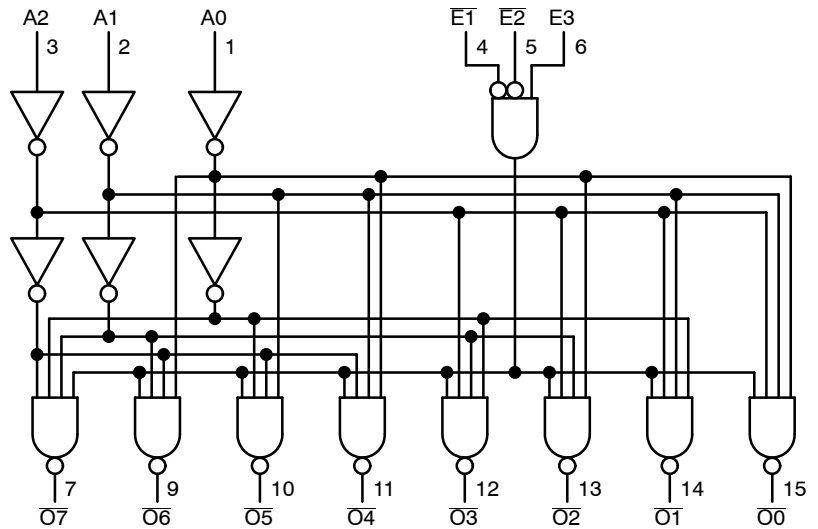

Figure 1. Pinout: 16−Lead (Top View)

Figure 2. Logic Diagram

PIN NAMES

Pins	Function
A0−A2	Address Inputs
E1−E2	Enable Inputs
E3	Enable Input
O0−O7	Outputs

TRUTH TABLE

Inputs						Outputs							
$\overline{E1}$	$\overline{E2}$	E3	A0	A1	A2	$\overline{O0}$	$\overline{O1}$	$\overline{O2}$	$\overline{O3}$	$\overline{O4}$	$\overline{O5}$	$\overline{O6}$	$\overline{O7}$
H	X	X	X	X	X	H	H	H	H	H	H	H	H
X	H	X	X	X	X	H	H	H	H	H	H	H	H
X	X	L	X	X	X	H	H	H	H	H	H	H	H
L	L	H	L	L	L	L	H	H	H	H	H	H	H
L	L	H	H	L	L	H	L	H	H	H	H	H	H
L	L	H	L	H	L	H	H	L	H	H	H	H	H
L	L	H	H	H	L	H	H	H	L	H	H	H	H
L	L	H	L	L	H	H	H	H	H	L	H	H	H
L	L	H	H	L	H	H	H	H	H	H	L	H	H
L	L	H	L	H	H	H	H	H	H	H	H	L	H
L	L	H	H	H	H	H	H	H	H	H	H	H	L

H = High Voltage Level
L = Low Voltage Level
X = High or Low Voltage Level and Transitions are Acceptable

For I_{CC} reasons, DO NOT FLOAT Inputs
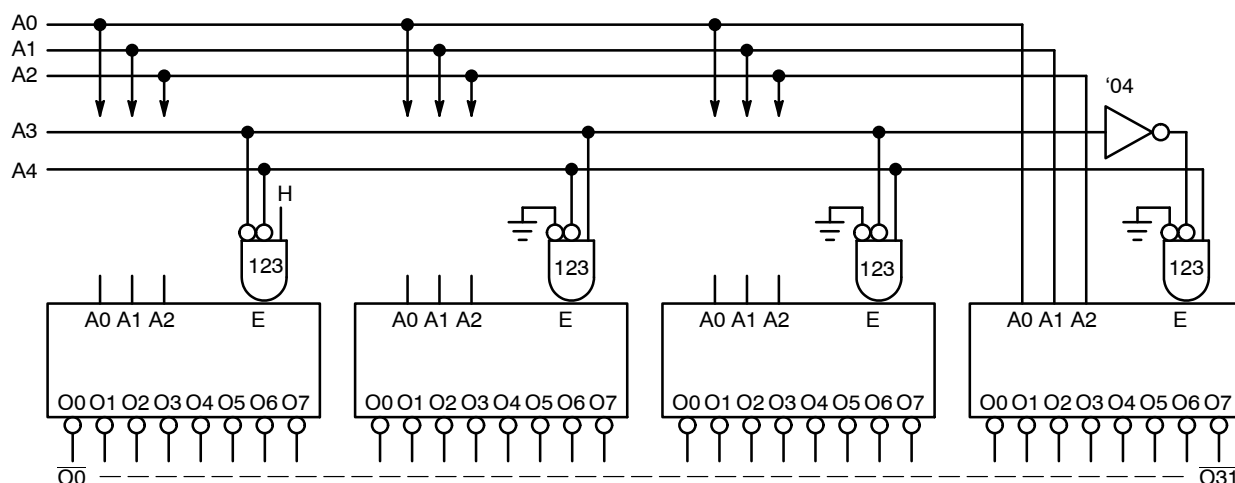
MC74LCX138

Figure 3. Expansion to 1−of−32 Decoding

ORDERING INFORMATION

Device	Package	Shipping[†]
MC74LCX138DR2G	SOIC−16 (Pb−Free)	2500 Tape & Reel
MC74LCX138DTG	TSSOP−16 (Pb−Free)	96 Units / Rail
MC74LCX138DTR2G	TSSOP−16 (Pb−Free)	2500 Tape & Reel
NLV74LCX138DR2G*	SOIC−16 (Pb−Free)	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Units
V_{CC}	DC Supply Voltage	−0.5 to +7.0		V
V_I	DC Input Voltage	$-0.5 \leq V_I \leq +7.0$		V
V_O	DC Output Voltage	$-0.5 \leq V_O \leq V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1)	V
I_{IK}	DC Input Diode Current	−50	$V_I < GND$	mA
I_{OK}	DC Output Diode Current	−50	$V_O < GND$	mA
		+50	$V_O > V_{CC}$	mA
I_O	DC Output Source/Sink Current	±50		mA
I_{CC}	DC Supply Current Per Supply Pin	±100		mA
I_{GND}	DC Ground Current Per Ground Pin	±100		mA
T_{STG}	Storage Temperature Range	−65 to +150		°C
MSL	Moisture Sensitivity		Level 1	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Typ	Max	Units
V_{CC}	Supply Voltage	Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	3.6 3.6	V
V_I	Input Voltage		0		5.5	V
V_O	Output Voltage	(HIGH or LOW State) (3–State)	0		V_{CC}	V
I_{OH}	HIGH Level Output Current	V_{CC} = 3.0 V – 3.6 V V_{CC} = 2.7 V – 3.0 V V_{CC} = 2.3 V – 2.7 V			−24 −12 −8	mA
I_{OL}	LOW Level Output Voltage	V_{CC} = 3.0 V – 3.6 V V_{CC} = 2.7 V – 3.0 V V_{CC} = 2.3 V – 2.7 V			+24 +12 +8	mA
T_A	Operating Free–Air Temperature		−40		+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, V_{IN} from 0.8 V to 2.0 V, V_{CC} = 3.0 V		0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic	Condition	T_A = −40°C to +85°C		Units
			Min	Max	
V_{IH}	HIGH Level Input Voltage (Note 2)	2.3 V ≤ V_{CC} ≤ 2.7 V	1.7		V
		2.7 V ≤ V_{CC} ≤ 3.6 V	2.0		
V_{IL}	LOW Level Input Voltage (Note 2)	2.3 V ≤ V_{CC} ≤ 2.7 V		0.7	V
		2.7 V ≤ V_{CC} ≤ 3.6 V		0.8	
V_{OH}	HIGH Level Output Voltage	2.3 V ≤ V_{CC} ≤ 3.6 V; I_{OH} = −100 µA	V_{CC} − 0.2		V
		V_{CC} = 2.3 V; I_{OH} = −8 mA	1.8		
		V_{CC} = 2.7 V; I_{OH} = −12 mA	2.2		
		V_{CC} = 3.0 V; I_{OH} = −18 mA	2.4		
		V_{CC} = 3.0 V; I_{OH} = −24 mA	2.2		
V_{OL}	LOW Level Output Voltage	2.3 V ≤ V_{CC} ≤ 3.6 V; I_{OL} = 100 µA		0.2	V
		V_{CC} = 2.3 V; I_{OL} = 8 mA		0.6	
		V_{CC} = 2.7 V; I_{OL} = 12 mA		0.4	
		V_{CC} = 3.0 V; I_{OL} = 16 mA		0.4	
		V_{CC} = 3.0 V; I_{OL} = 24 mA		0.55	
I_{OFF}	Power Off Leakage Current	V_{CC} = 0, V_{IN} = 5.5 V or V_{OUT} = 5.5 V		10	µA
I_{IN}	Input Leakage Current	V_{CC} = 3.6 V, V_{IN} = 5.5 V or GND		±5	µA
I_{CC}	Quiescent Supply Current	V_{CC} = 3.6 V, V_{IN} = 5.5 V or GND		10	µA
ΔI_{CC}	Increase in I_{CC} per Input	2.3 ≤ V_{CC} ≤ 3.6 V; V_{IH} = V_{CC} − 0.6 V		500	µA

2. These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS (t_R = t_F = 2.5 ns; R_L = 500 Ω)

Symbol	Parameter	Waveform	Limits						Units
			T_A = −40°C to +85°C						
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 2.5 V ± 0.2 V		
			C_L = 50 pF		C_L = 50 pF		C_L = 30 pF		
			Min	Max	Min	Max	Min	Max	
t_{PLH} t_{PHL}	Propagation Delay An to $\overline{On}$	1, 2	1.5 1.5	6.0 6.0	1.5 1.5	7.0 7.0	1.5 1.5	7.2 7.2	ns
t_{PLH} t_{PHL}	Propagation Delay E1, E2 to $\overline{On}$	2	1.5 1.5	6.5 6.5	1.5 1.5	7.5 7.5	1.5 1.5	8.4 8.4	ns
t_{PLH} t_{PHL}	Propagation Delay E3 to $\overline{On}$	1	1.5 1.5	6.0 6.0	1.5 1.5	7.0 7.0	1.5 1.5	7.2 7.2	ns
t_{OSHL} t_{OSLH}	Output–to–Output Skew (Note 3)			1.0 1.0					ns

3. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH–to–LOW (t_{OSHL}) or LOW–to–HIGH (t_{OSLH}); parameter guaranteed by design.
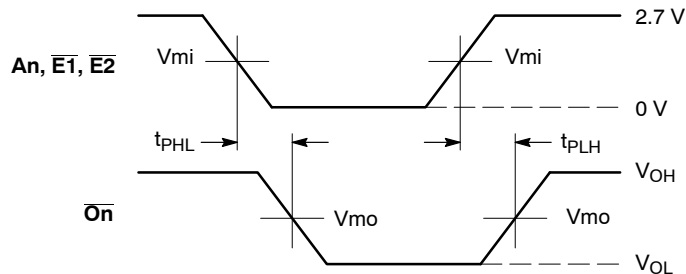
MC74LCX138

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C_{IN}	Input Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	7	pF
C_{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	8	pF
C_{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	25	pF
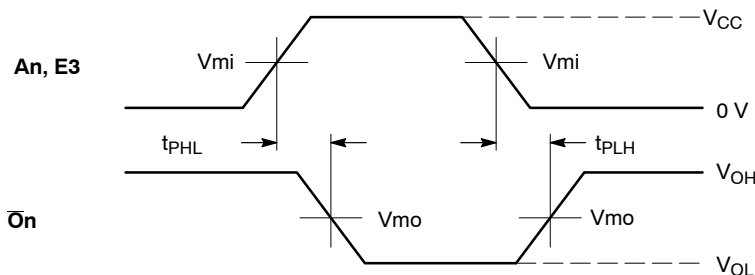
WAVEFORM 1: PROPAGATION DELAYS FOR INVERTING OUTPUTS

WAVEFORM 2: PROPAGATION DELAYS FOR NON–INVERTING OUTPUTS

Symbol	Vcc		
	3.3 V ± 0.3 V	2.7 V	2.5 V ± 0.2 V
Vmi	1.5 V	1.5 V	Vcc/2
Vmo	1.5 V	1.5 V	Vcc/2

Figure 4. AC Waveforms
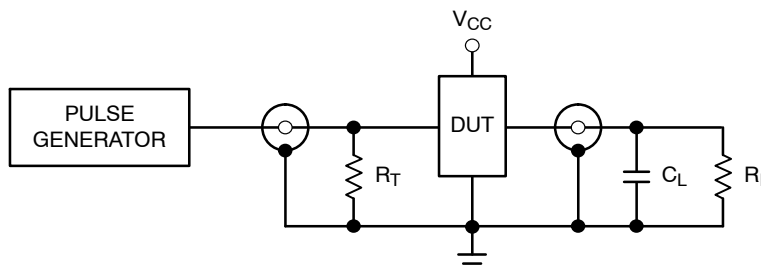
C_L = 50 pF at V_{CC} = 3.3 ± 0.3 V or equivalent (includes jig and probe capacitance)
C_L = 30 pF at V_{CC} = 2.5 ± 0.2 V or equivalent (includes jig and probe capacitance)
R_L = R_1 = 500 Ω or equivalent
R_T = Z_{OUT} of pulse generator (typically 50 Ω)

Figure 5. Test Circuit
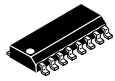
SOIC−16
CASE 751B−05
ISSUE K
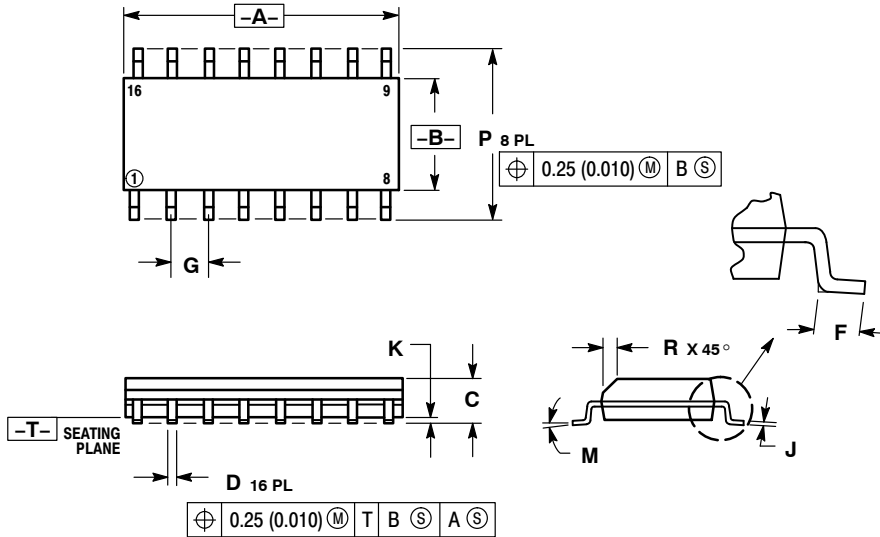
SCALE 1:1

DATE 29 DEC 2006

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:
PIN 1. COLLECTOR
2. BASE
3. EMITTER
4. NO CONNECTION
5. EMITTER
6. BASE
7. COLLECTOR
8. COLLECTOR
9. BASE
10. EMITTER
11. NO CONNECTION
12. EMITTER
13. BASE
14. COLLECTOR
15. EMITTER
16. COLLECTOR

STYLE 2:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION
4. CATHODE
5. CATHODE
6. NO CONNECTION
7. ANODE
8. CATHODE
9. CATHODE
10. ANODE
11. NO CONNECTION
12. CATHODE
13. CATHODE
14. NO CONNECTION
15. ANODE
16. CATHODE

STYLE 3:
PIN 1. COLLECTOR, DYE #1
2. BASE, #1
3. EMITTER, #1
4. COLLECTOR, #1
5. COLLECTOR, #2
6. BASE, #2
7. EMITTER, #2
8. COLLECTOR, #2
9. COLLECTOR, #3
10. BASE, #3
11. EMITTER, #3
12. COLLECTOR, #3
13. COLLECTOR, #4
14. BASE, #4
15. EMITTER, #4
16. COLLECTOR, #4

STYLE 4:
PIN 1. COLLECTOR, DYE #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. COLLECTOR, #3
6. COLLECTOR, #3
7. COLLECTOR, #4
8. COLLECTOR, #4
9. BASE, #4
10. EMITTER, #4
11. BASE, #3
12. EMITTER, #3
13. BASE, #2
14. EMITTER, #2
15. BASE, #1
16. EMITTER, #1

STYLE 5:
PIN 1. DRAIN, DYE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. DRAIN, #3
6. DRAIN, #3
7. DRAIN, #4
8. DRAIN, #4
9. GATE, #4
10. SOURCE, #4
11. GATE, #3
12. SOURCE, #3
13. GATE, #2
14. SOURCE, #2
15. GATE, #1
16. SOURCE, #1

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. CATHODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE
15. ANODE
16. ANODE

STYLE 7:
PIN 1. SOURCE N-CH
2. COMMON DRAIN (OUTPUT)
3. COMMON DRAIN (OUTPUT)
4. GATE P-CH
5. COMMON DRAIN (OUTPUT)
6. COMMON DRAIN (OUTPUT)
7. COMMON DRAIN (OUTPUT)
8. SOURCE P-CH
9. SOURCE P-CH
10. COMMON DRAIN (OUTPUT)
11. COMMON DRAIN (OUTPUT)
12. COMMON DRAIN (OUTPUT)
13. GATE N-CH
14. COMMON DRAIN (OUTPUT)
15. COMMON DRAIN (OUTPUT)
16. SOURCE N-CH

SOLDERING FOOTPRINT

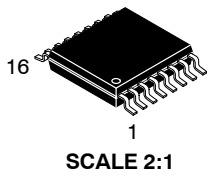DIMENSIONS: MILLIMETERS
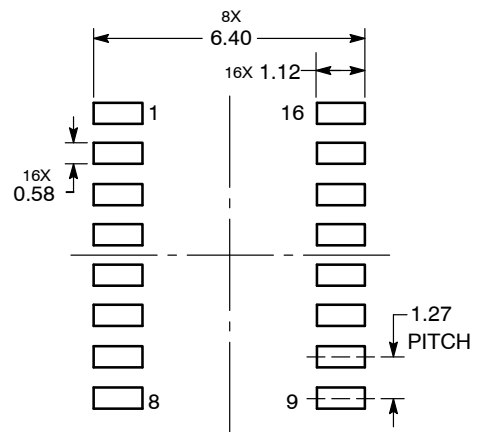
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DESCRIPTION:	SOIC−16		**PAGE 1 OF 1**

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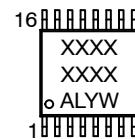# MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

TSSOP−16
CASE 948F−01
ISSUE B

DATE 19 OCT 2006
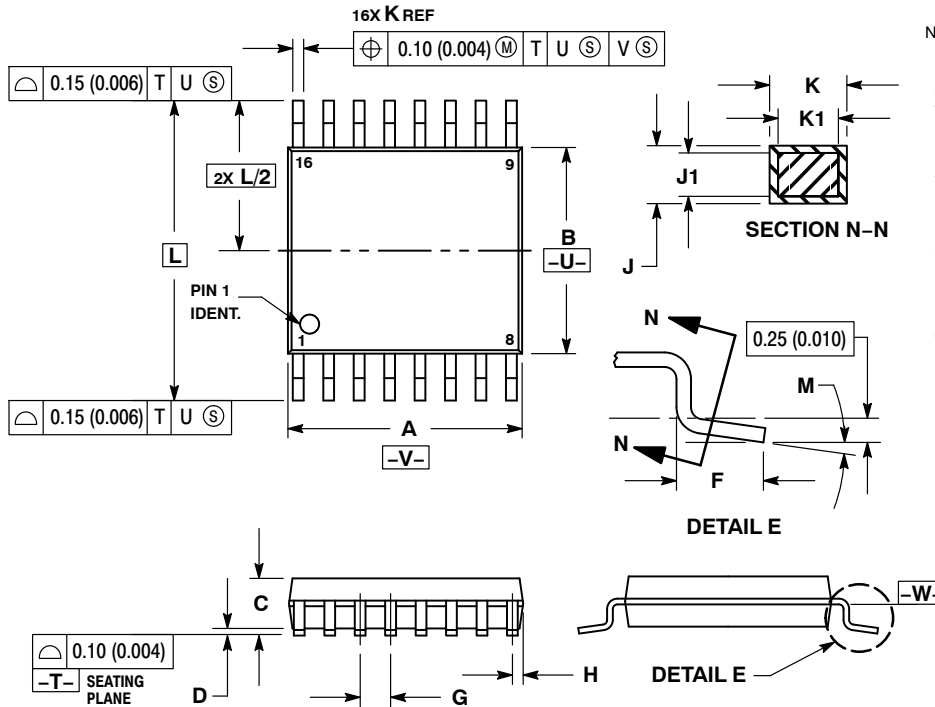
16

1

SCALE 2:1

16X **K** REF

⊕ 0.10 (0.004) Ⓜ T U Ⓢ V Ⓢ

⬜ 0.15 (0.006) T U Ⓢ

2X **L/2**

L

16

9

B
−U−

PIN 1
IDENT.

1

8

⬜ 0.15 (0.006) T U Ⓢ

A
−V−

K

K1

J1

J

SECTION N−N

N

0.25 (0.010)

M

N

F

DETAIL E

C

⬜ 0.10 (0.004)
−T− SEATING
PLANE

D

G

H

DETAIL E

−W−

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SOLDERING FOOTPRINT

7.06

1

0.65
PITCH

16X
0.36

16X
1.26

DIMENSIONS: MILLIMETERS
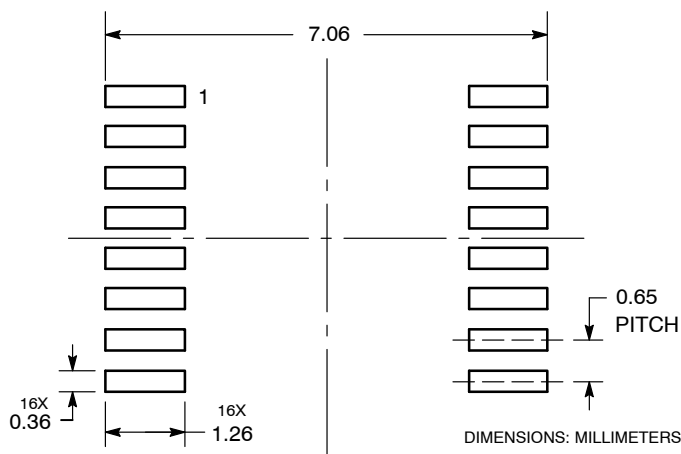
GENERIC MARKING DIAGRAM*

16

XXXX
XXXX
ALYW

1

XXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
G or ▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot " ▪", may or may not be present.

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PUBLICATION ORDERING INFORMATION

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